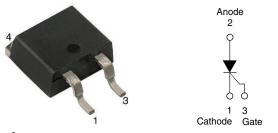
Vishay Semiconductors

Thyristor Surface-Mount, Phase Control SCR, 16 A



www.vishay.com

D²PAK 2L (TO-263AB 2L)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{T(AV)}	16 A							
V _{DRM} /V _{RRM}	1600 V							
V _{TM}	1.25 V							
I _{GT}	45 mA							
TJ	-40 °C to +125 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single SCR							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS16S2L-M3 high voltage series of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS						
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0							

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	16	٨						
I _{RMS}		25	A						
V _{RRM} /V _{DRM}		1600	V						
I _{TSM}		350	А						
V _T	16 A, T _J = 25 °C	1.25	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA
VS-25TTS16SLHM3	1600	1600	10

Revision: 25-Aug-2021

1

Document Number: 96891

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT HALOGEN

FREE



VS-25TTS16S2LHM3

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEO	T CONDITIONS	VAL	UNITS	
PARAMETER	STMBUL	163	CONDITIONS	TYP.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6	
Maximum RMS on-state current	I _{RMS}			2	5	А
Maximum peak, one-cycle,		10 ms sine pulse, r	ated V _{RRM} applied	3	00	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, r	no voltage reapplied	3	50	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, r	ated V _{RRM} applied	450		A ² s
	1-1	10 ms sine pulse, r	630		A-5	
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms	6300		A²√s	
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.25		V
On-state slope resistance	r _t	12.0		2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C	1j= 125 C		.0	V
Maximum reverse and direct lockage surrent	1 /1	T _J = 25 °C		0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		1
Holding current	I _H	Anode supply = 6 V, resistive load, initial $I_T = 1 \text{ A}$, $T_J = 25 \text{ °C}$		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = Open$			V/µs
Maximum rate of rise of turned-on current	dl/dt			1	A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T_J = - 10 °C	60		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	45	mA	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \degree C$	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0	V	
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}		0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs				
Typical turn-off time	tq	1j=125 C	110					

Revision: 25-Aug-2021 Document Number: 96891 2 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

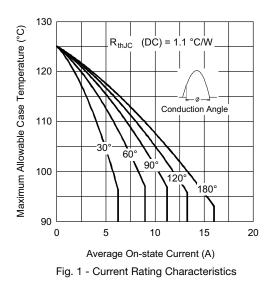


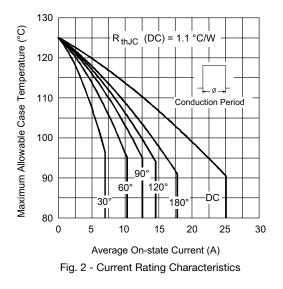
Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS						
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Soldering temperature	Τ _S	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	0/10				
Approximate weight			2	g				
			0.07	oz.				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	25TT	S16S				

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W





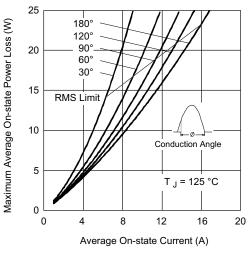
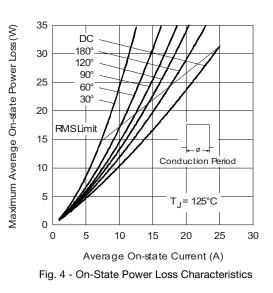


Fig. 3 - On-State Power Loss Characteristics



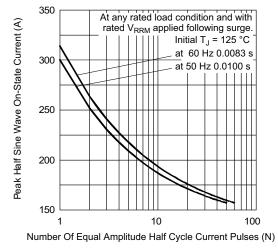
Revision: 25-Aug-2021

3

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

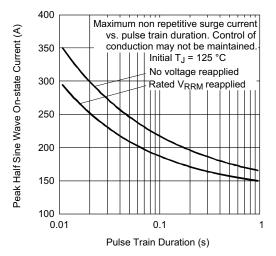
VS-25TTS16S2LHM3

Vishay Semiconductors



www.vishay.com







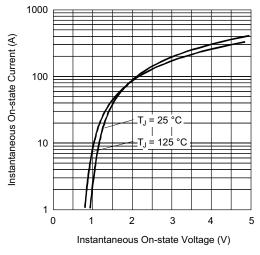
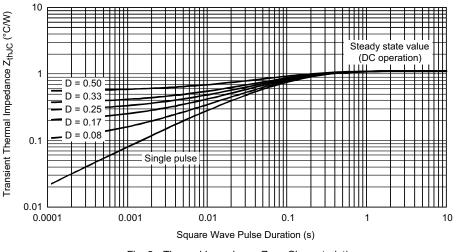


Fig. 7 - On-State Voltage Drop Characteristics





Revision: 25-Aug-2021 **4** Document Number: 96891 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-25TTS16S2LHM3

Vishay Semiconductors

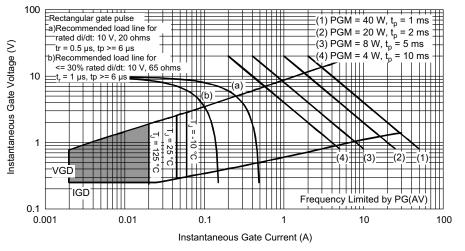


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

www.vishay.com

SHAY

Device code	VS-	25	т	т	s	16	S	2	L	н	М3
	1	2	3	4	5	6	7	8	9	10	(11)
	1 -	· Visł	nay Sen	niconduc	ctors pro	oduct					
	2 -	- Cur	rent rati	ng (25 =	= 25 A)						
	3 -	 Circuit configuration: T = single thyristor 									
	4	· Pac	Package: T = D^2 PAK (TO-263AB)								
	5 -	. Тур	e of silio	con:	,	ifier					
	6		S = standard recovery rectifier Voltage rating: Voltage code x 100 = V _{RRM} — 16 = 1600 V								
	7 -	- S =	surface	mounta	able						
	8 -	2 =	true 2 p	in D ² PA	K						
	9 -	L =	L = tape and reel (left oriented), for different orientation contact factory								
	10 -	• H=	H = AEC Q101 qualified								
	11 -			ntal digit en-free,		complia	nt, and	termina	tions lea	ad (Pb)-	free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS16S2LHM3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?96317						

Revision: 25-Aug-2021

Document Number: 96891

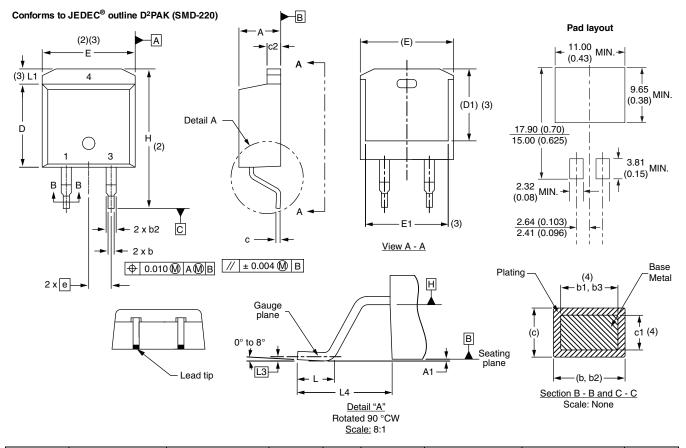
For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

Vishay Semiconductors



D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	ICHES NOTES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.25 BSC 0.010 BSC		
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

Revision: 14-Mar-2022

1

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.